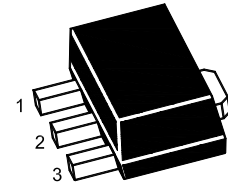


# 2SA1666U

## PNP Silicon Epitaxial Planar Power Transistor

### Features

- The transistor is subdivided into two groups, O and Y, according to its DC current gain.



1.Base 2.Collector 3.Emitter  
SOT-89 Plastic Package

### Applications

- For high current

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

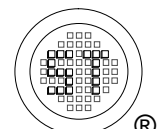
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	2	A
Base Current	$-I_B$	0.4	A
Total Power Dissipation	$P_{tot}$	0.5 <sup>1)</sup> 1 <sup>2)</sup>	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	250 <sup>1)</sup> 125 <sup>2)</sup>	$^\circ\text{C/W}$

<sup>1)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

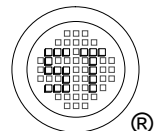
<sup>2)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



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## Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 2\text{ V}$ , $-I_C = 500\text{ mA}$  at $-V_{CE} = 2\text{ V}$ , $-I_C = 1.5\text{ A}$	Current Gain Group O	$h_{FE}$	70	-	140	-
	Y	$h_{FE}$	120	-	240	-
		$h_{FE}$	40	-	-	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	-	100	nA	
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA	
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	50	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	$-V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V	
Collector Emitter Saturation Voltage at $-I_C = 1\text{ A}$ , $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Base Emitter Saturation Voltage at $-I_C = 1\text{ A}$ , $-I_B = 50\text{ mA}$	$-V_{BE(sat)}$	-	-	1.2	V	
Transition Frequency at $-V_{CE} = 2\text{ V}$ , $-I_C = 500\text{ mA}$	$f_T$	-	120	-	MHz	
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	40	-	pF	



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## Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

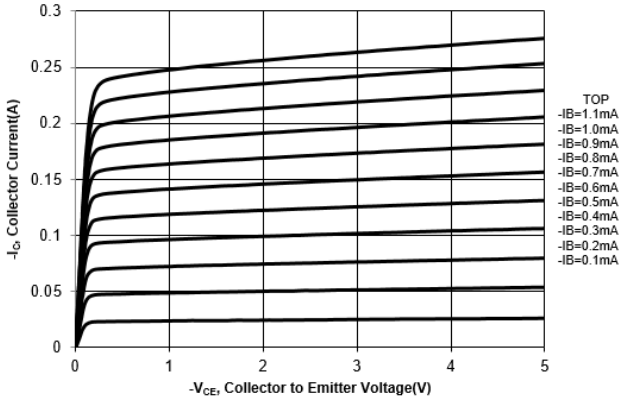


Fig. 2 Collector Current vs. Base to Emitter Voltage

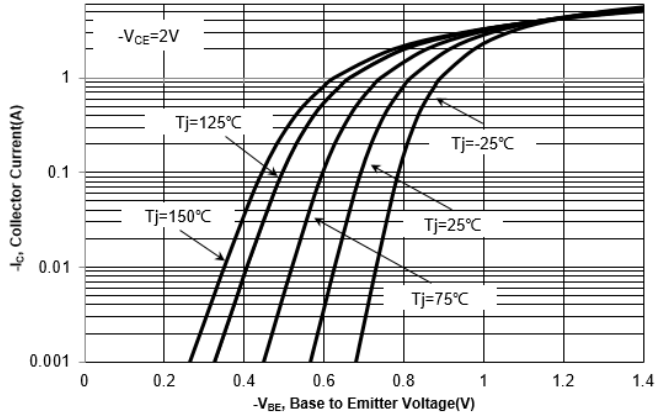


Fig. 3 DC Current Gain vs. Collector Current

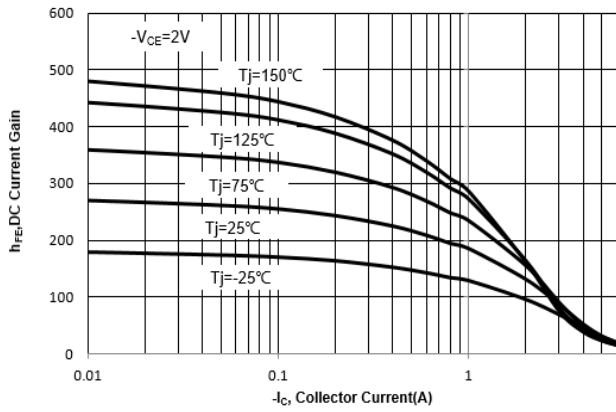
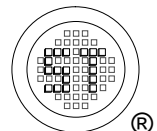
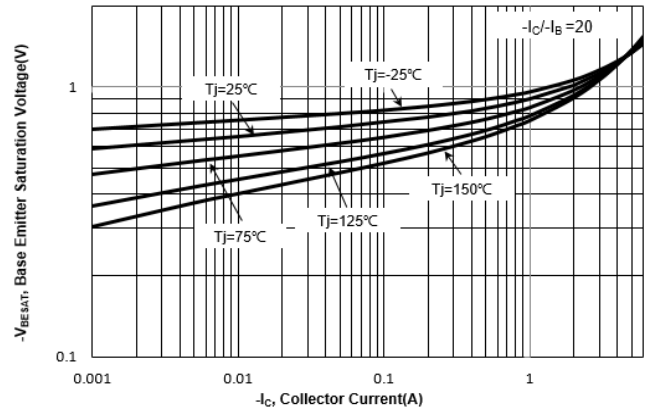


Fig. 4  $V_{BESAT}$  vs. Collector Current



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## Electrical Characteristics Curves

Fig. 5  $V_{CESAT}$  vs. Collector Current

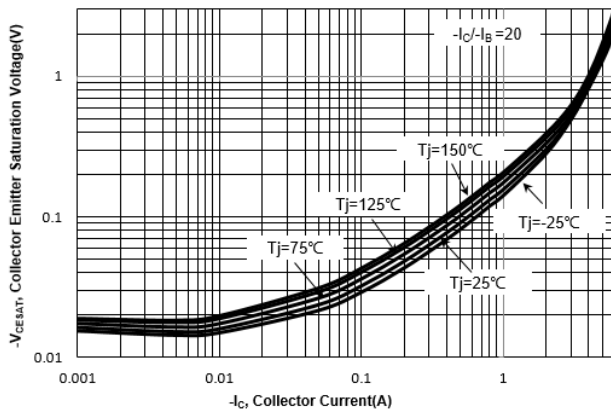


Fig. 6 Output Capacitance

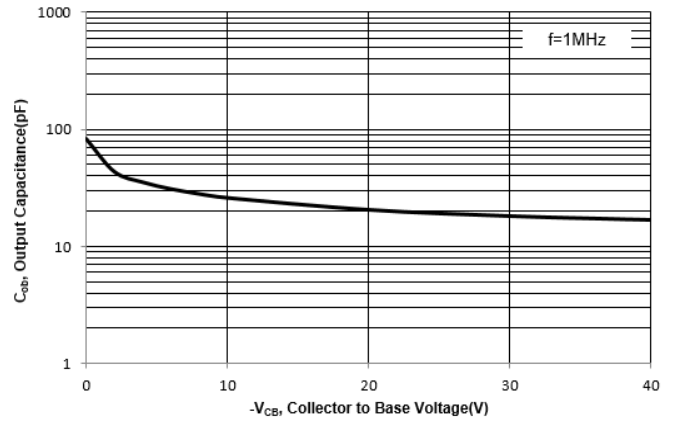
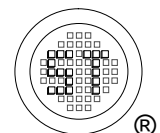
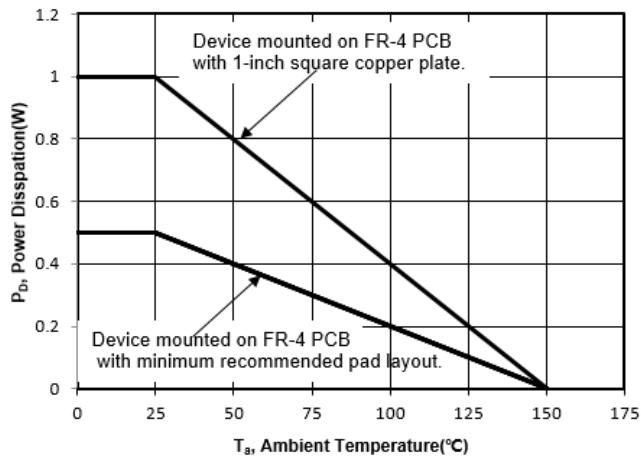


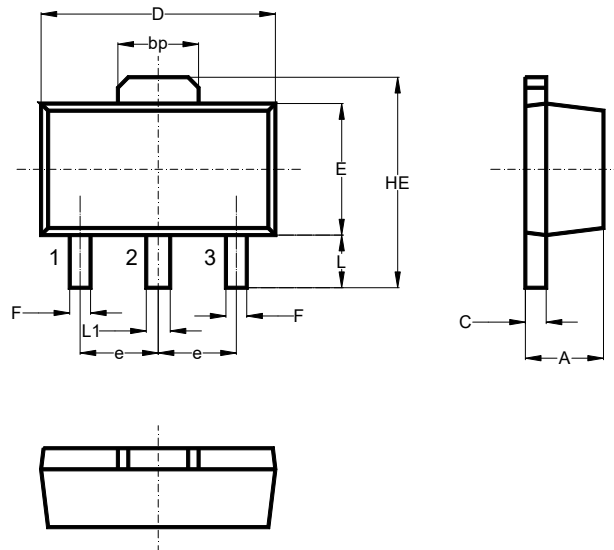
Fig. 7 Power Derating Curve



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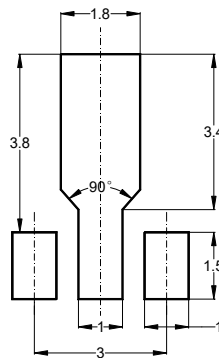
## Package Outline (Dimensions in mm)

SOT-89



Unit	A	bp	C	D	E	F	HE	e	L	L1
mm	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

### Recommended Soldering Footprint



### Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-89	12	8 ± 0.1	0.315 ± 0.004	178	7	1,000
				330	13	4,000

### Marking information

" 2SA1666\*U " = Part No. (" \* " = HFE grouping Code)

" YM " = Date Code Marking

" Y " = Year

" M " = Month

Font type: Arial

